

Data sheet	
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2N5460/5461/5462

P-channel J-FETs

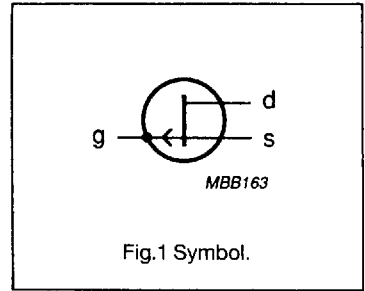
DESCRIPTION

P-channel silicon junction field-effect transistor in a TO-92 plastic envelope. It is intended for use as an analog switch and an amplifier.

PINNING - TO-92

PIN	DESCRIPTION
1	gate
2	drain
3	source

PIN CONFIGURATION



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LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$\pm V_{DS}$	drain-source voltage		-	40	V
V_{GS}	gate-source voltage		-	40	V
$-I_G$	gate current		-	10	mA
P_{tot}	total power dissipation	$T_{amb} \leq 40\text{ }^\circ\text{C}$	-	310	mW
T_{stg}	storage temperature range		-65	150	$^\circ\text{C}$
T_j	junction temperature		-	150	$^\circ\text{C}$

THERMAL RESISTANCE

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-a}$	from junction to ambient	355	K/W

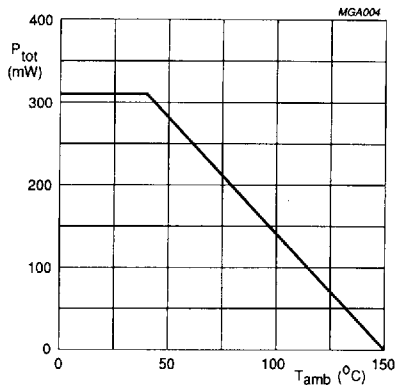


Fig.2 Total power dissipation as a function of ambient temperature.

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CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{GSS}	gate-source leakage current	$V_{GS} = 20\text{ V}$ $V_{DS} = 0$	-	5	nA
		$V_{GS} = 20\text{ V}$ $V_{DS} = 0$ $T_{amb} = 100\text{ }^{\circ}\text{C}$	-	1	μA
$-I_{DSS}$	drain-source leakage current	$-V_{DS} = 15\text{ V}$ $V_{GS} = 0$	1	5	mA
		2N5460	2	9	mA
		2N5461 2N5462	4	16	mA
V_{GS}	gate-source voltage	$-I_D = 0.1\text{ mA}$ $-V_{DS} = 15\text{ V}$	0.5	4	V
V_{GS}	gate-source voltage	$-I_D = 0.2\text{ mA}$ $-V_{DS} = 15\text{ V}$	0.8	4.5	V
V_{GS}	gate-source voltage	$-I_D = 0.4\text{ mA}$ $-V_{DS} = 15\text{ V}$	1.5	6	V
$V_{P(GS)}$	gate-source cut-off voltage	$-I_D = 1\text{ }\mu\text{A}$ $-V_{DS} = 15\text{ V}$	0.75	6	V
		2N5460	1	7.5	V
		2N5461 2N5462	1.8	9	V
$ y_{fs} $	transfer admittance	$-V_{DS} = 15\text{ V}$ $V_{GS} = 0$	1	4	mS
		2N5460	1.5	5	mS
		2N5461 2N5462	2	6	mS
$ y_{os} $	output admittance	$-V_{DS} = 15\text{ V}$ $V_{GS} = 0$ $f = 1\text{ kHz}$	-	75	μS
C_{iss}	input capacitance	$-V_{DS} = 15\text{ V}$ $V_{GS} = 0$ $f = 1\text{ MHz}$	-	7	pF
C_{rss}	feedback capacitance	$-V_{DS} = 15\text{ V}$ $V_{GS} = 0$ $f = 1\text{ MHz}$	-	2	pF
NF	noise figure	$-V_{DS} = 15\text{ V}$ $V_{GS} = 0$ $f = 100\text{ Hz}$ $B = 1\text{ Hz}$	-	2.5	dB